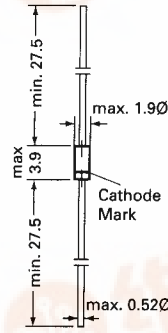


# ST 60 P SILICON SCHOTTKY BARRIER DIODE

## Silicon Schottky Barrier Diode

Characteristics equivalent to or better than 1N60P ideal for used in detection or for switching on the radio, TV, etc..



Glass case JEDEC DO-35

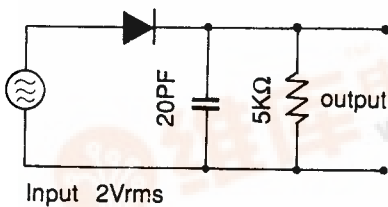
Dimensions in mm

## Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RM}$	45	V
Reverse Voltage dc	$V_R$	20	V
Peak Forward Current	$I_{FM}$	150	mA
Average Rectified Output Current	$I_O$	50	mA
Surge Forward Current	$I_{surge}$	500	mA
Junction Temperature	$T_J$	75	$^\circ\text{C}$
Storage Temperature Range	$T_S$	-55 to + 175	$^\circ\text{C}$

## Characteristics

	Symbol	Test condition ( $T_a 25 \pm 2\text{ }^\circ\text{C}$ )	Min.	Typ.	Max.	Units
Forward Current	$I_F$	$V_F = 1\text{V}$	4	-	-	mA
Reverse Currents	$I_R$	$V_R = 10\text{V}$	-	-	50	$\mu\text{A}$
Junction Capacitance C	-	$f = 1\text{MHz}, V = 1\text{V}$	-	-	1	PF
Rectification efficiency	$\eta$	$V_i = 2\text{Vrms}, = 5\text{K}\Omega$ $C = 20\text{PF}, f = 40\text{ MHz}$	55	-	-	%



Rectification Efficiency Measurement Circuit